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Si-Ion Implantation Doping in α -Ga₂O₃ and Its Application to Fabrication of Low-Resistance Ohmic Contacts

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215	Research and development on Ga ₂ O ₃ transistors and diodes. 2013 ,		
214	Depletion-mode Ga ₂ O ₃ metal-oxide-semiconductor field-effect transistors on $\bar{\Gamma}$ Ga ₂ O ₃ (010) substrates and temperature dependence of their device characteristics. 2013 , 103, 123511		454
213	Depletion-mode Ga ₂ O ₃ MOSFETs on $\bar{\Gamma}$ Ga ₂ O ₃ (010) substrates with Si-ion-implanted channel and contacts. 2013 ,		25
212	Crystal Growth and Device Application of Gallium Oxide (Ga ₂ O ₃). 2014 , 35, 102-107		
211	Band alignment and electrical properties of Al ₂ O ₃ / $\bar{\Gamma}$ Ga ₂ O ₃ heterojunctions. 2014 , 104, 192104		139
210	Doping of Ga ₂ O ₃ bulk crystals and NWs by ion implantation. 2014 ,		7
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